

1. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of from  $\sim 6 \times 10^{19} \text{ cm}^{-3}$  to  $\sim 3.75 \times 10^{20} \text{ cm}^{-3}$ .

2. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of less than  $\sim 3.75 \times 10^{20} \text{ cm}^{-3}$ .

11. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of greater than  $\sim 6 \times 10^{19} \text{ cm}^{-3}$ .

12. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a late implant doping technique.